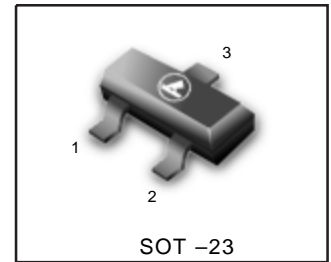


# Dual Serise Switching Diodes

## FEATURES

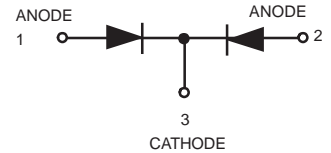
- Ultra high speed switching
- Suitable for high packing density layout.
- High reliability.
- We declare that the material of product is ROHS compliant.

**LDAN202KLT1G**



## DEVICE MARKING AND ORDERING INFORMATION

Device	Marking	Shipping
LDAN202KLT1G	N	3000/Tape&Reel
LDAN202KLT3G	N	10000/Tape&Reel



## MAXIMUM RATINGS (Each Diode)

Rating	Symbol	Value	Unit
Reverse Voltage	$V_R$	80	Vdc
Forward Current	$I_o$	100	mAdc
Peak Forward Surge Current	$I_{FM(surge)}$	300	mAdc
Forward voltage( $I_f = 100mA$ )	$V_F$	1.2	V
Reverse current ( $V_r = 70V$ )	$I_R$	0.1	$\mu A$
Capacitance between terminals( $f = 1MHz$ )	$C_T$	3.5	pF
Reverse recovery time( $V_r = 6V, I_f = 5 mA$ )	$T_{rr}$	4	nS

## ELECTRICAL CHARACTERISTIC CURVES

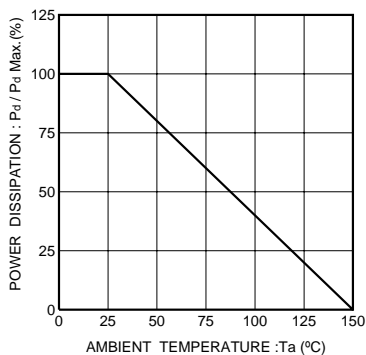


Fig.1 Power attenuation curve

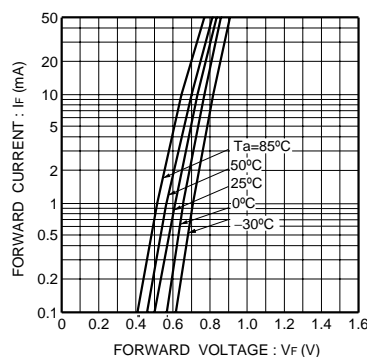


Fig.2 Forward characteristics (P Type)

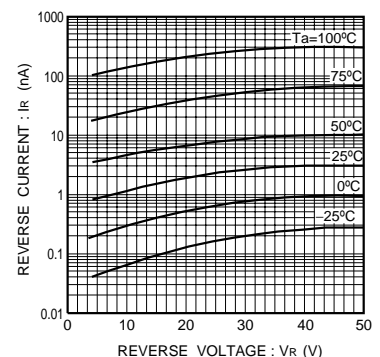


Fig.3 Reverse characteristics (P Type)

# LDAN202KLT1G

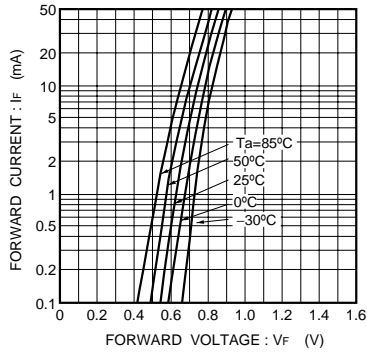


Fig.4 Forward characteristics (N Type)

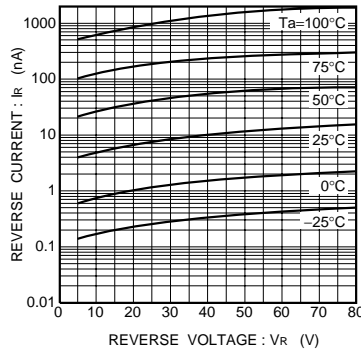


Fig.5 Reverse characteristics (N Type)

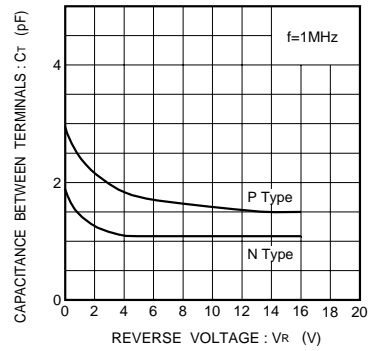


Fig.6 Capacitance between terminals characteristics

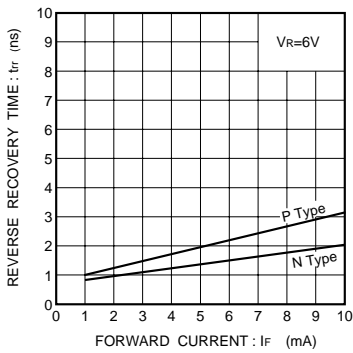


Fig.7 Reverse recovery time

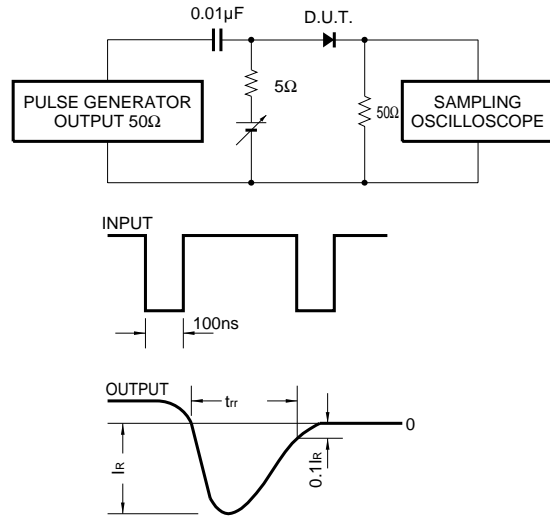


Fig.8 Reverse recovery time ( $t_{rr}$ ) measurement circuit

